

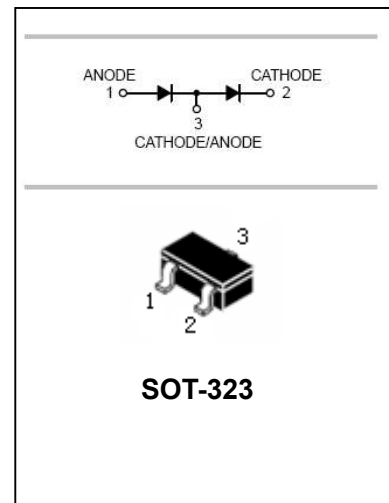
Dual series switching diode

FEATURES

- Fast switching speed.
- High conductance.
- Connected in series.
- Surface mount package ideally suited for automatic insertion.

APPLICATIONS

- ESD protection, polarity reversal protection, Data line protection, Inductive load protection.



ORDERING INFORMATION

Type No.	Marking	Package Code
BAV99W	KJG	SOT-323

MAXIMUM RATING @ Ta=25°C unless otherwise specified

Parameter	Symbol	Value	Unit
Repetitive peak reverse voltage	V_{RRM}	75	V
DC Reverse voltage	V_R	75	V
RMS Reverse Voltage	$V_{R(RMS)}$	53	V
Non-Repetitive forward surge current @t=1.0s @t=1.0ms @t=1.0μs	I_{FSM}	0.5 1.0 2.0	A
Peak forward surge current ^{Note1}	$I_{FM(surge)}$	300	mA
Repetitive peak forward surge current	I_{FRM}	450	mA
Forward continuous current	I_F	215	mA
Average rectified forward current (averaged over any 20ms period)	$I_{F(AV)}$	715	mA
Power dissipation	P_d	200	mW
Thermal resistance junction-to-ambient	$R_{\theta JA}$	625	°C/W
Operating and storage temperature range	T_j, T_{STG}	-65 to +150	°C

Note:1. Device mounted on FR-4 PC board with recommended pad layout

ELECTRICAL CHARACTERISTICS @ Ta=25°C unless otherwise specified

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Reverse breakdown voltage	$V_{(BR)}$	$I_{(BR)}=100\mu A$	75		V
Reverse voltage leakage current	I_R	$V_R=70V$		2.5	μA
Forward voltage	V_F	$I_F=1mA$ $I_F=10mA$ $I_F=50mA$ $I_F=150mA$		715 855 1000 1250	mV
Diode capacitance	C_D	$V_R=0V$ $f=1MHz$		1.5	pF
Reverse recovery time	t_{rr}	$I_F=I_R=10mA$ $R_L=100\Omega$		6.0	nS
Forward recovery voltage	V_{FR}	$I_F=10mA, t_r=20ns$		1.75	V

TYPICAL CHARACTERISTICS @ Ta=25°C unless otherwise specified

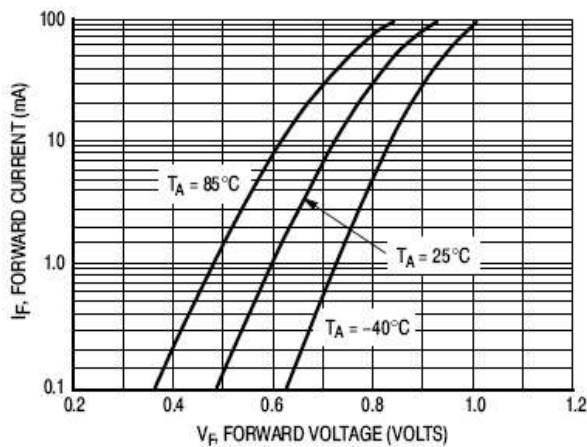


Figure 2. Forward Voltage

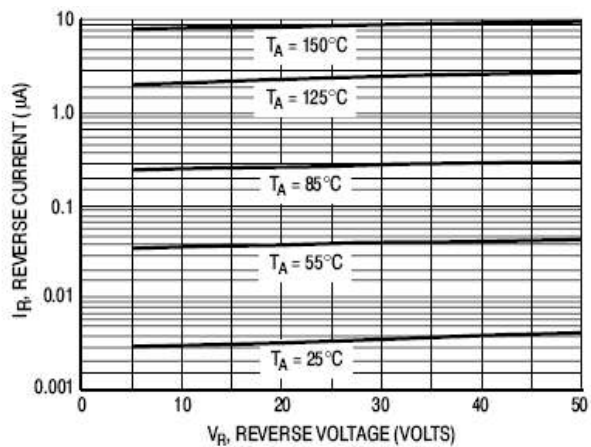


Figure 3. Leakage Current

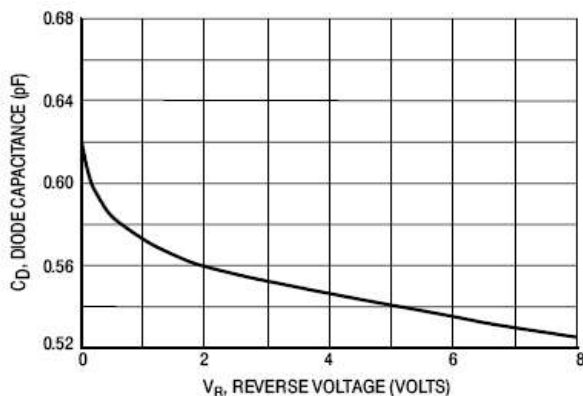
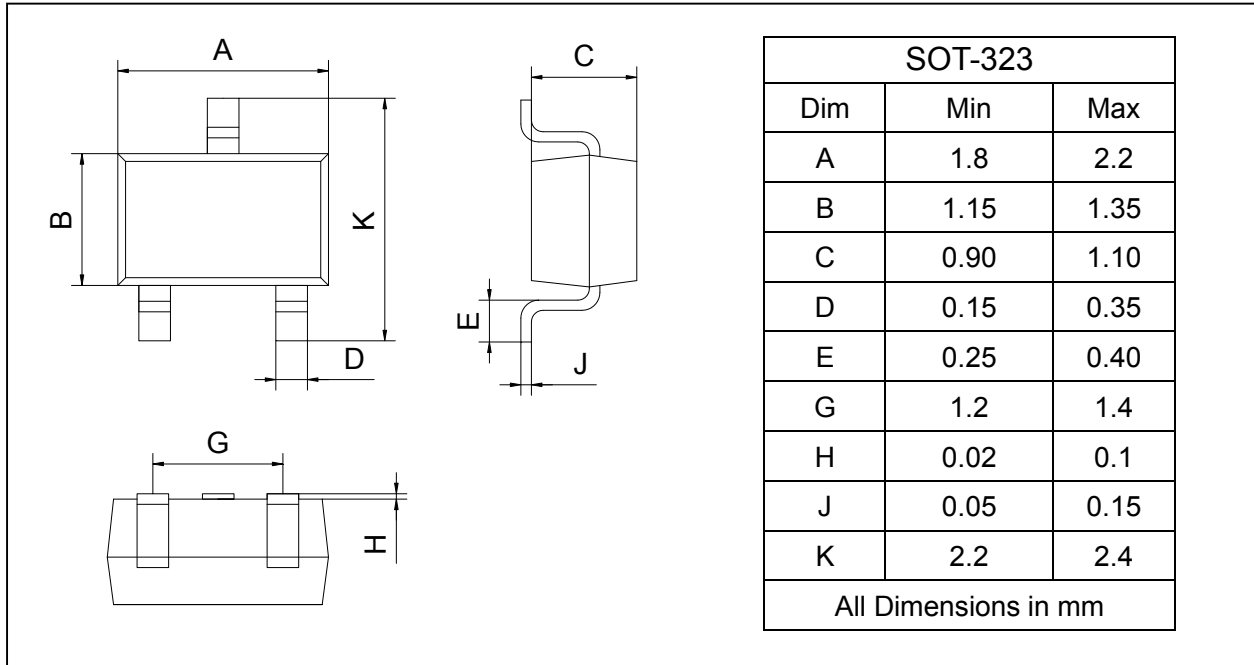


Figure 4. Capacitance

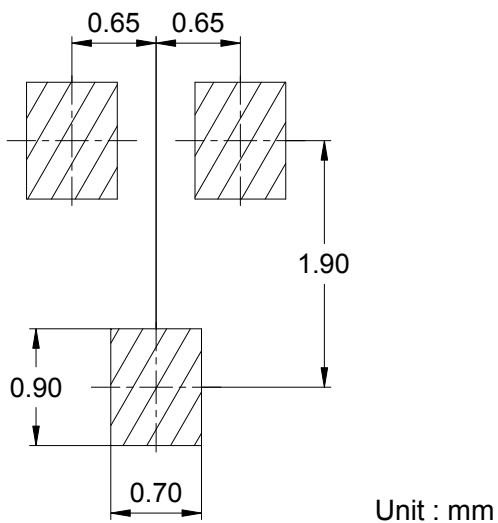
PACKAGE OUTLINE

Plastic surface mounted package

SOT-323



SOLDERING FOOTPRINT



PACKAGE INFORMATION

Device	Package	Shipping
BAV99W	SOT-323	3000/Tape&Reel